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Stress Induced Phenomena and Reliability in 3D Microelectronics

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Editors

Paul S. Ho
University of Texas, Texas, USA

Chao-Kun Hu
IBM T.J. Watson Research Center, New York, USA

Mark Nakamoto
Qualcomm Incorporated, California, USA

Shinichi Ogawa
Advanced Industrial Science and Technology, Ibaraki, Japan

Valeriy Sukharev
Mentor Graphics Corporation, California, USA

Larry Smith
SEMATECH, New York, USA

Ehrenfried Zschech
Fraunhofer Institute for Ceramic Technologies and Systems, Dresden, Germany

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Editors

Paul S. Ho
University of Texas at Austin
Microelectronics Research Center
Mechanical Engineering Department
10100 Burnet Road, Bldg. 160
Austin, Texas 78758
USA

E-mail: hops@austin.utexas.edu

Chao-Kun Hu
IBM T.J. Watson Research Center
1101 Kitchawan Road, Route 134
Yorktown Heights, NY 10598
USA

E-mail: haohu@us.ibm.com

Mark Nakamoto
Qualcomm Inc.
5775 Morehouse Drive, R-106E
San Diego, CA 92121-1714
USA

E-mail: nakamoto@qti.qualcomm.com

Shinichi Ogawa
Advanced Industrial Science and Technology (AIST)
West 7A, 16-1 Onogawa, Tsukuba
Ibaraki, 305-8569
Japan

E-mail: ogawa.shinichi@aist.go.jp

Valeriy Sukharev
Mentor Graphics Corporation
46871 Bayside Parkway
Fremont, CA 94538
USA

E-mail: Valeriy_Sukharev@mentor.com

Larry Smith
SEMATECH
3D Interconnect Division
257 Fuller Road, Suite 2200
Albany, NY 12203
USA

E-mail: larry.smith@alum.mit.edu

Ehrenfried Zschech
Fraunhofer Institute for Ceramic Technologies and Systems IKTS
Maria-Reiche-Strasse 2
D-01109 Dresden,
Germany

E-mail: Ehrenfried.Zschech@ikts-md.fraunhofer.de

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